



10/A  
B.H.  
Docket No. 50369 7-12-01

THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: E. Pavelchek  
SERIAL NO.: 09/330,417 GROUP: 1746  
FILED: June 11, 1999 EXAMINER: M. Kornakov  
FOR: ANTIREFLECTIVE HARD MASK COMPOSITIONS

Honorable Commissioner of Patents and Trademarks  
Washington, DC 20231

Sir:

AMENDMENT

Applicant is in receipt of the Office Action dated January 4, 2001. Please amend the above-identified application as follows.

**IN THE SPECIFICATION**

At page 3, line 14, please delete "geranium" and insert therefore -germanium--.

**IN THE CLAIMS**

✓ / ✓ / ✓  
Please cancel claims 2, 3 and 21-23 without prejudice.

- Sub B1  
A1
1. (amended) A method for etching a dielectric layer overlying an integrated circuit or electronic packaging substrate, comprising:
    - (a) providing an integrated circuit substrate having a dielectric layer thereon;
    - (b) over the dielectric layer, depositing a coating layer of an inorganic antireflective hard mask composition that comprises one or more inorganic elements selected from Group IIIa, IVa, Va, VIIA, VIII, Ib, IIb, IIIb, IVb, or Vb of the Periodic Table, the antireflective composition comprising at least about 5 mole percent of inorganic atoms, based on total solids of the antireflective composition;
    - (c) depositing a coating layer of a photoresist composition over the antireflective hard mask composition coating layer;